

#### **Features**

- · Split Gate Trench MOSFET Technology
- · Excellent Package for Heat Dissipation
- High Density Cell Design for Low R<sub>DS(ON)</sub>
- Halogen Free. "Green" Device (Note 1)
- · Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- · Moisture Sensitivity Level 1

# **Maximum Ratings**

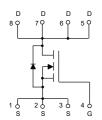
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 2.8°C/W Junction to Case<sup>(2)</sup>

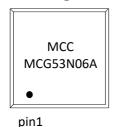
Parameter		Symbol	Rating	Unit	
Drain-Source Voltage		V <sub>DS</sub>	60	V	
Gate-Source Volltage		V <sub>GS</sub>	±20	V	
Continuous Drain Current	T <sub>C</sub> =25°C	- I <sub>D</sub>	53	A	
	T <sub>C</sub> =100°C	J D	33		
Pulsed Drain Current <sup>(3)</sup>	I <sub>DM</sub>	186	Α		
Total Power Dissipation		P <sub>D</sub>	45	W	
Single Pulsed Avalanche Energy <sup>(4)</sup>		E <sub>AS</sub>	162	mJ	

#### Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. Surface Mounted on 1 in<sup>2</sup> pad area, t ≤10 sec.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4.  $V_{DD}$ =50V,  $R_G$ =25 $\Omega$ , L=1mH,  $I_{AS}$ =18A.

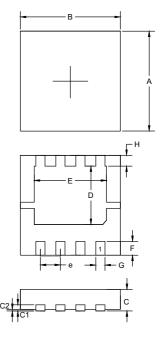
## **Internal Structure and Marking Code**





# N-CHANNEL MOSFET

## **DFN3333**



DIMENSIONS					
DIM INCHES		HES	MM		NOTE
DIIVI	MIN	MAX	MIN	MAX	NOTE
Α	0.126	0.130	3.20	3.30	
В	0.126	0.130	3.20	3.30	
С	0.030	0.033	0.75	0.85	
C1	0.007	0.009	0.18	0.22	
C2		0.002		0.05	
D	0.071	0.079	1.80	2.00	
Е	0.087	0.098	2.20	2.50	
F	0.016	0.020	0.40	0.50	
G	0.010	0.014	0.25	0.35	
Н	0.012	0.016	0.30	0.40	
е	0.024	0.028	0.60	0.70	

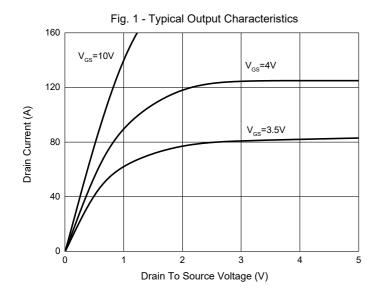


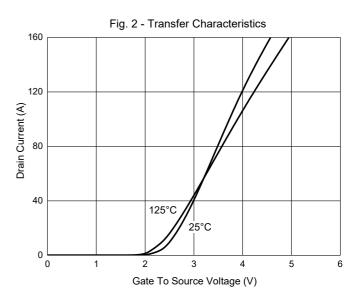
# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

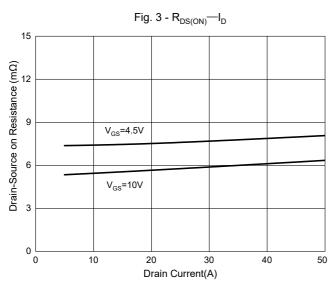
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics			1		1		
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60			V	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1	μA	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1.2	1.7	2.5	V	
Drain-Source On-Resistance		V <sub>GS</sub> =10V, I <sub>D</sub> =20A		5.8	8.2	mΩ	
	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A		7.3	12	mΩ	
Gate Resistance	R <sub>g</sub>	V <sub>DS</sub> =0V,V <sub>GS</sub> =0V,f=1MHZ		1.6		Ω	
Diode Characteristics			·				
Continuous Body Diode Current	Is				53	Α	
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A			1.3	V	
Reverse Recovery Time	t <sub>rr</sub>	L 00A II / II 000A/		36		ns	
Reverse Recovery Charge	Q <sub>rr</sub>	l <sub>F</sub> =20A, dl <sub>F</sub> /dt=200A/μs		27		nC	
Dynamic Characteristics			·				
Input Capacitance	C <sub>iss</sub>			2000		pF	
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =35V,V <sub>GS</sub> =0V,f=1MHz		390			
Reverse Transfer Capacitance	C <sub>rss</sub>			13			
Total Gate Charge	Qg			34			
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =10V,I <sub>D</sub> =20A		7.8		nC	
Gate-Drain Charge	$Q_{gd}$			5.2			
Turn-On Delay Time	t <sub>d(on)</sub>			10			
Turn-On Rise Time	t <sub>r</sub>	$V_{DS}$ =30V, $V_{GS}$ =10V, $R_{G}$ =3 $\Omega$ , $I_{DS}$ =12A		36		<b></b>	
Turn-Off Delay Time	t <sub>d(off)</sub>	11G-012, IDS-12A		30		ns	
Turn-Off Fall Time	t <sub>f</sub>			57			

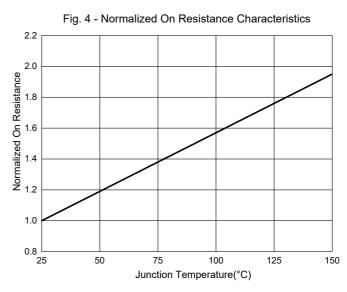


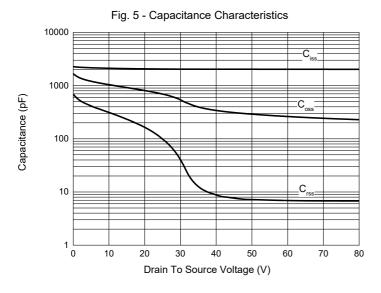
#### **Curve Characteristics**

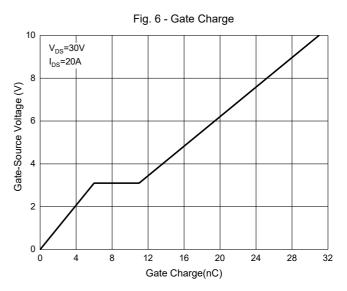








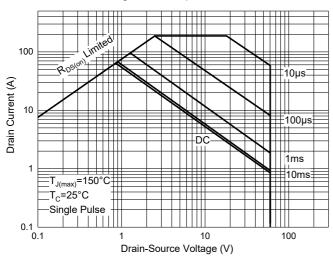






# **Curve Characteristics**







## **Ordering Information**

Device	Packing	
Part Number-TP	Tape&Reel: 5Kpcs/Reel	

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